Role of Quantum Confinement Effect on Tunneling Operation of LTFET Devices

Faraz Najam · Yun Seop Yu
Hankyong National University
E-mail: ysyu@hknu.ac.kr

ABSTRACT

Part of the channel in L-shaped tunnel field-effect transistor (LTFET) is very thin and suffers from quantum confinement effect. Role of quantum confinement effect on band-to-band-tunneling (BTBT) of LTFET was investigated using numerical simulation and band diagram analysis. It was found that quantum confinement effect significantly affects the BTBT mechanism of LTFET devices.

Keywords
BTBT, LTFET, potential, quantum confinement

I. Introduction

L-shaped tunnel field-effect transistor (LTFET) has been introduced[1] to overcome the low on current $I_{ON}$ problem of conventional TFETs. In this work, the effect of quantum confinement (QC) on band-to-band-tunneling (BTBT) mechanism of LTFET is investigated using numerical simulation[2].

II. Quantum Confinement Effect

Fig. 1 shows schematic of LTFET. As can be seen in Fig. 1, there is a part of the channel labelled as region II in Fig. 1 that is very thin that is only 4 nm. This part of the channel suffers from QC effect. Whereas, region III which is also part of the chanel does not suffer from QC effect.

QC effect increases the bandgap near the surface where all the BTBT paths terminate. As a result, it becomes difficult for the BTBT condition $E_c=E_v$ (E_v valence band) to be met in region II. because conduction band edge $E_c$ is raised around surface whereas, within the source which does not suffer from QC it remains unchanged; a more raised $E_c$ needs an equivalent $E_v$ for BTBT to take place. Hence, for a majority of the gate bias swing, region II does not conduct. However, region III which does not suffer from QC conducts for all bias values. Region II only conducts when the gate bias is very high.

III. Results

Fig. 2(a) and (b) show BTBT contour plots when quantum model is not selected and when quantum model is selected, respectively, at a gate-source voltage $V_{gs}=0.4$ V and drain-source voltage $V_{ds}=0.25$ V. With quantum model selected BTBT is not present. With no quantum model selected, a finite BTBT is observed in region II. Fig. 3 shows the band diagram extracted from the simulator in region II along -0.010 μm $\leq x \leq 0.0$ μm, $y=0.0$ μm in $x$, and $y$ directions respectively at $V_{gs}=0.4$ V and $V_{ds}=0.25$ V with quantum model selected (Fig. 3(a)) and with no quantum model selected (Fig. 3(b)). eQuantumpotential is the correction added to $E_c$ when positive [2]. It can clearly be seen in Fig. 3(a) that $E_c$ increases around the surface with quantum model selected, hence BTBT cannot take place in region II.

IV. Conclusion

It was found that due to quantum confinement, BTBT does not take place in region II until $V_{gs}$ bias is very high. Whereas,
BTBT takes place in region III for all biases.

References


![Fig. 1. Schematic of LTFET.](image)

![Fig. 2. BTBT contour plots extracted from the simulator at $V_{gs}=0.40$ V and $V_{ds}=0.25$ V. (a) No quantum model selected. (b) Quantum model selected.](image)

![Fig. 3 Band diagram extracted from the simulator at $V_{gs}=0.40$ V. (a) Quantum model selected. (b) No quantum model selected.](image)